Simulasi model : Heterojunction bipolar transistor silikon - germanium (HBT SiGe) berdasarkan pengaturan lebar stripe emiter (We)

Abstrak

Si-Ge HBTs is an electronic device having important role in developing Information and Telecommunication Technology. It can be shown by the superior performance of threshold frequency (fr) oscillation frequency (fosc) current gain (B) and minimum noise figure (Fn)....